



PMCXB1000UE

30 V, complementary N/P-channel Trench MOSFET

27 June 2016

Product data sheet

1. General description

Complementary N/P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Very low threshold voltage for portable applications: $V_{GS(th)} = 0.7 \text{ V}$
- Leadless ultra small and ultra thin SMD plastic package: $1.1 \times 1.0 \times 0.37 \text{ mm}$
- ElectroStatic Discharge (ESD) protection $> 2 \text{ kV HBM}$

3. Applications

- Relay driver
- High-speed line driver
- Level shifter
- Power management in battery-driven portables

4. Quick reference data

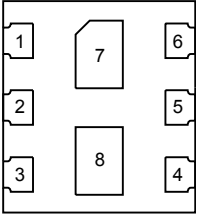
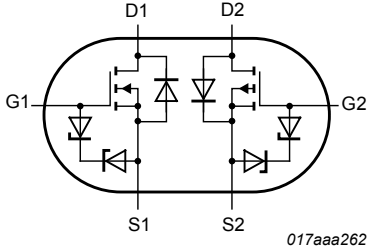
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
TR1 (N-channel), Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 590 \text{ mA}; T_j = 25 \text{ }^\circ\text{C}$	-	550	670	$\text{m}\Omega$
TR2 (P-channel), Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -410 \text{ mA}; T_j = 25 \text{ }^\circ\text{C}$	-	1.2	1.4	Ω
TR1 (N-channel)						
V_{DS}	drain-source voltage	$T_j = 25 \text{ }^\circ\text{C}$	-	-	30	V
I_D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$	[1]	-	590	mA
TR2 (P-channel)						
V_{DS}	drain-source voltage	$T_j = 25 \text{ }^\circ\text{C}$	-	-	-30	V
I_D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$	[1]	-	-410	mA

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm^2 .

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	 Transparent top view DFN1010B-6 (SOT1216)	
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1		
7	D1	drain TR1		
8	D2	drain TR2		

6. Ordering information

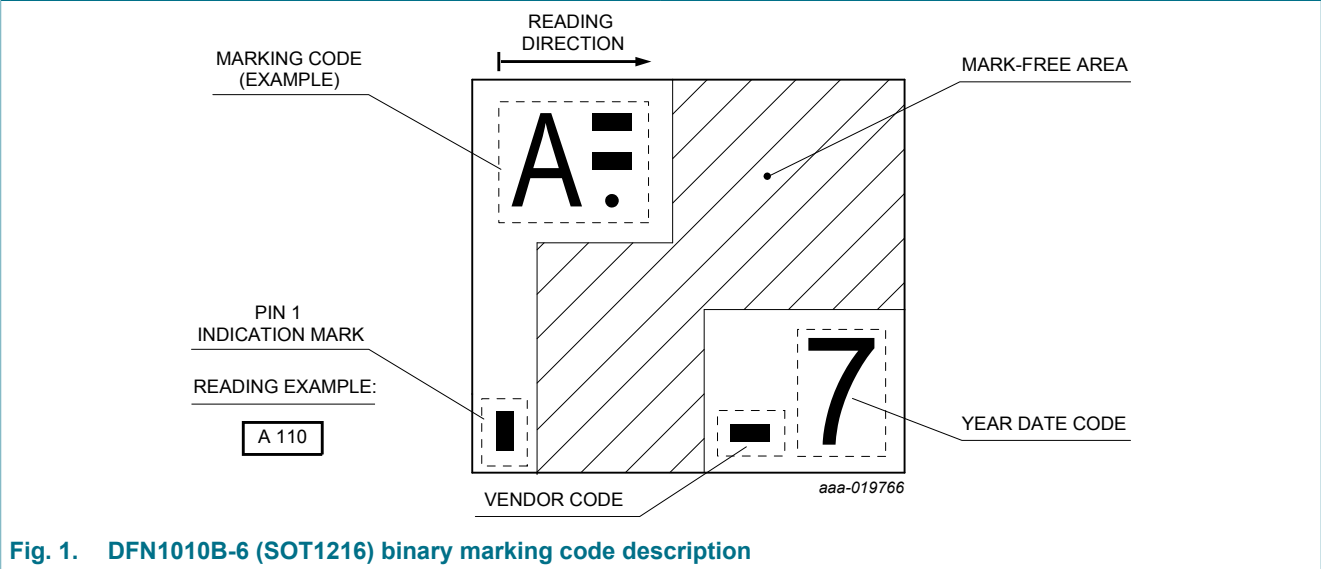
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMCXB1000UE	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

7. Marking

Table 4. Marking codes

Type number	Marking code
PMCXB1000UE	B 101



8. Limiting values

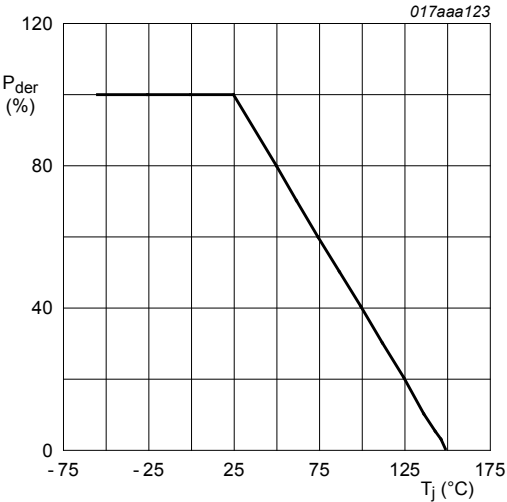
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
TR1 (N-channel)						
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	590	mA
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	370	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	2.3	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	285	mW
			[1]	-	410	mW
		T _{sp} = 25 °C		-	4	W
TR2 (P-channel)						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-410	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-260	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-1.7	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	285	mW
			[1]	-	410	mW
		T _{sp} = 25 °C		-	4	W
Per device						
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
TR1 (N-channel), Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	380	mA
TR2 (P-channel), Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	-410	mA

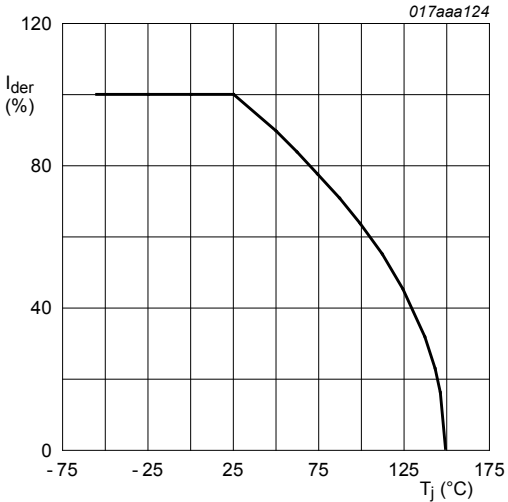
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm^2 .

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$

Fig. 2. MOSFET transistor: Normalized total power dissipation as a function of junction temperature



$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100 \%$$

Fig. 3. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

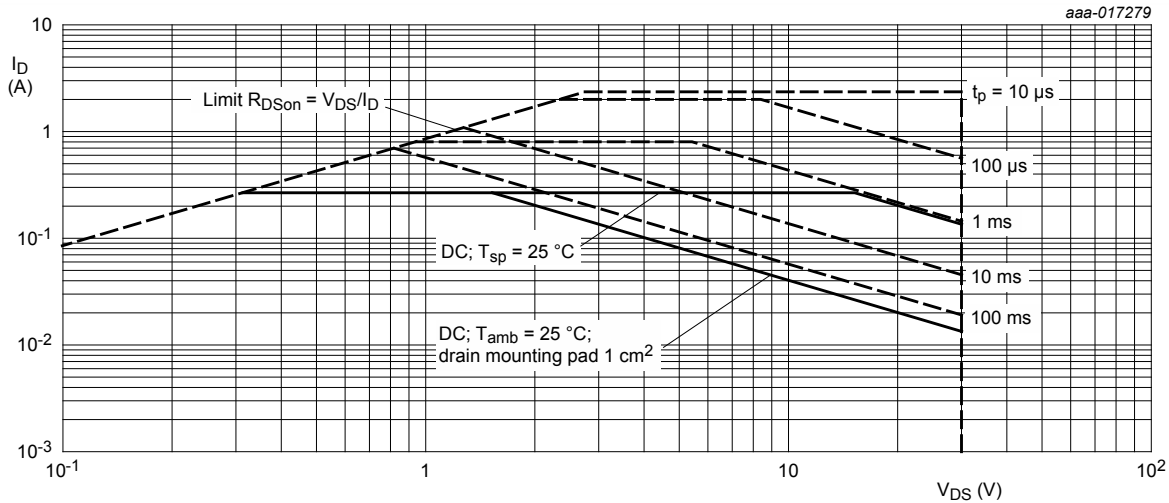
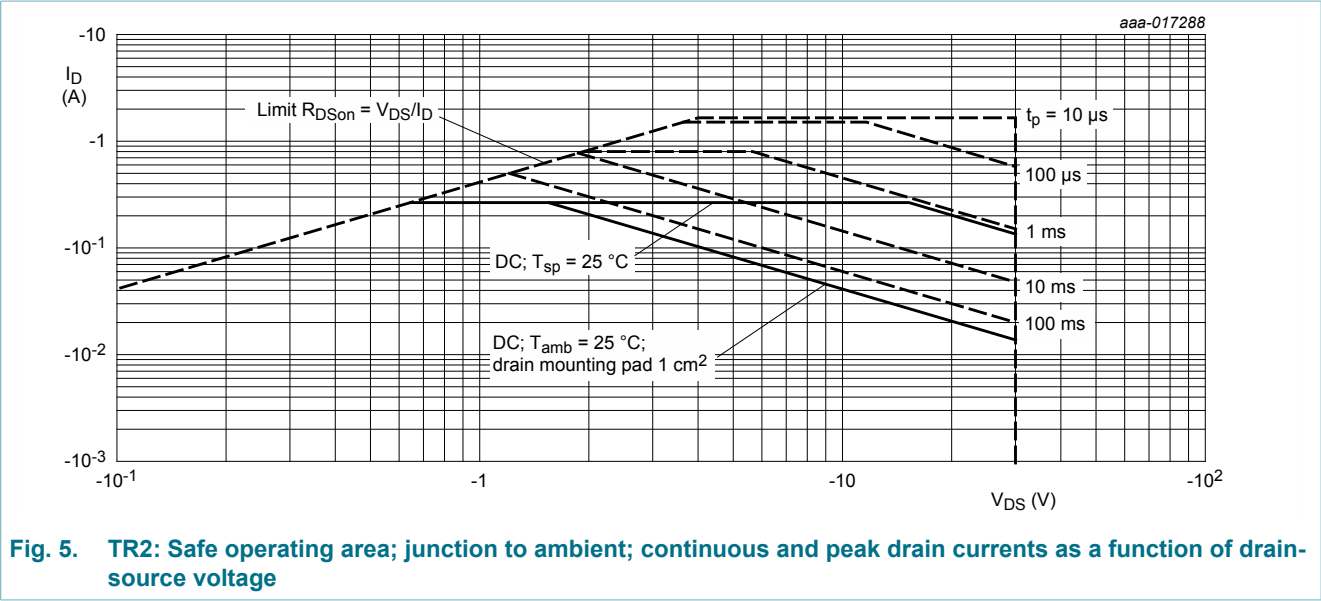


Fig. 4. TR1: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

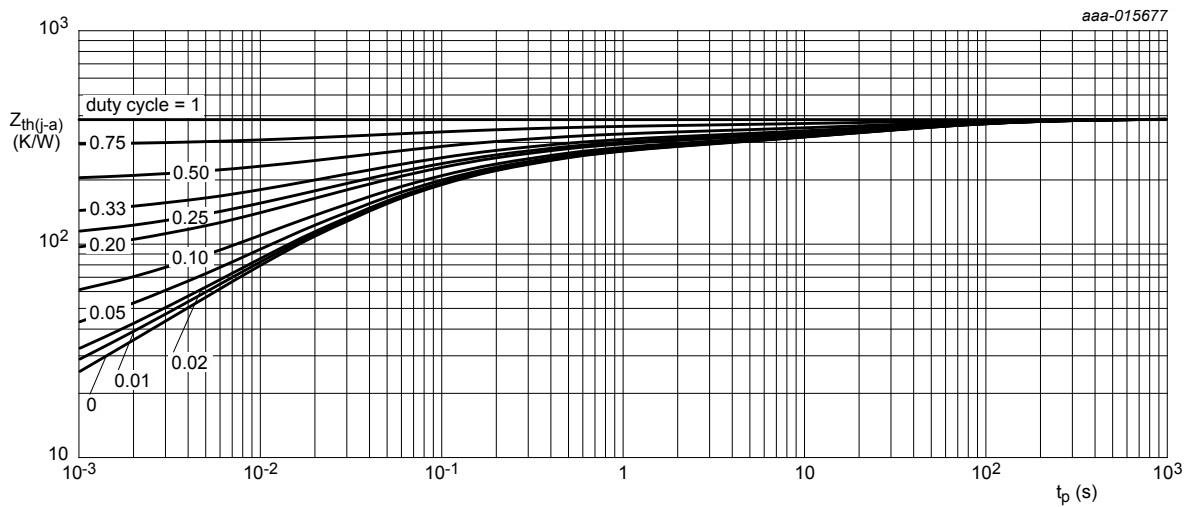


9. Thermal characteristics

Table 6. Thermal characteristics

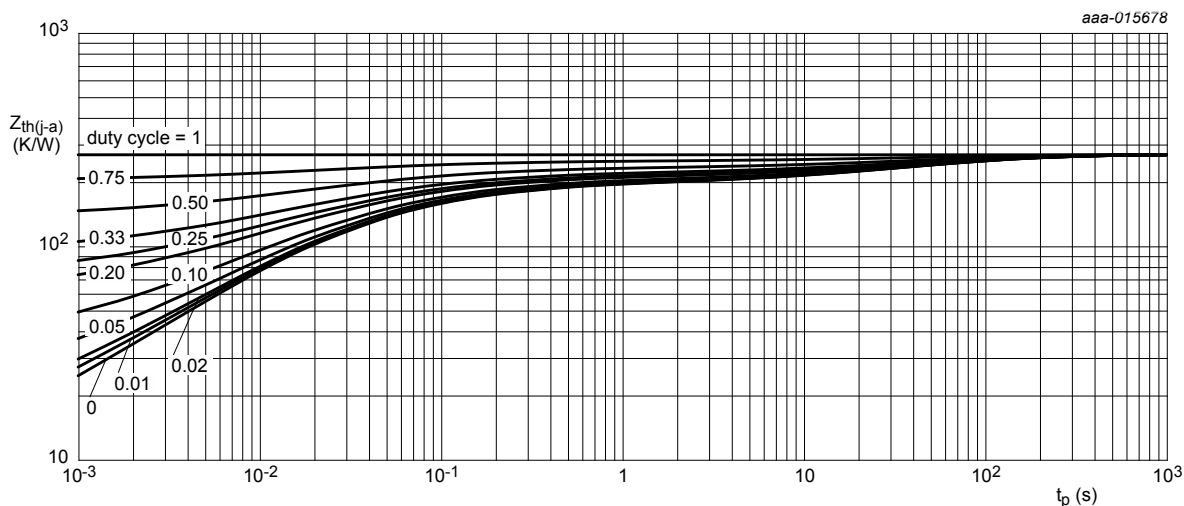
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
TR1 (N-channel)							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	380	440	K/W
			[2]	-	275	305	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	27	31	K/W
TR2 (P-channel)							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	380	440	K/W
			[2]	-	275	305	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	27	31	K/W

[1] Device mounted on an FR4 PCB, single-sided copper; tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig. 6. TR1 and TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 7. TR1 and TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
TR1 (N-channel), Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu A$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250\ \mu A$; $V_{DS} = V_{GS}$; $T_j = 25\ ^\circ C$	0.45	0.7	0.95	V
I_{DSS}	drain leakage current	$V_{DS} = 30\ V$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	1	μA
I_{GSS}	gate leakage current	$V_{GS} = 8\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	5	μA
		$V_{GS} = -8\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-5	μA
		$V_{GS} = 4.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	1	μA
		$V_{GS} = -4.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-1	μA
		$V_{GS} = 2.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	100	nA
		$V_{GS} = -2.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\ V$; $I_D = 590\ mA$; $T_j = 25\ ^\circ C$	-	550	670	m Ω
		$V_{GS} = 4.5\ V$; $I_D = 590\ mA$; $T_j = 150\ ^\circ C$	-	960	1170	m Ω
		$V_{GS} = 2.5\ V$; $I_D = 590\ mA$; $T_j = 25\ ^\circ C$	-	660	900	m Ω
		$V_{GS} = 1.8\ V$; $I_D = 80\ mA$; $T_j = 25\ ^\circ C$	-	770	1120	m Ω
		$V_{GS} = 1.5\ V$; $I_D = 10\ mA$; $T_j = 25\ ^\circ C$	-	890	1500	m Ω
g_{fs}	forward transconductance	$V_{DS} = 10\ V$; $I_D = 590\ mA$; $T_j = 25\ ^\circ C$	-	600	-	mS
TR2 (P-channel), Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250\ \mu A$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250\ \mu A$; $V_{DS} = V_{GS}$; $T_j = 25\ ^\circ C$	-0.45	-0.7	-0.95	V
I_{DSS}	drain leakage current	$V_{DS} = -30\ V$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-1	μA
I_{GSS}	gate leakage current	$V_{GS} = 8\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	5	μA
		$V_{GS} = -8\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-5	μA
		$V_{GS} = 4.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	1	μA
		$V_{GS} = -4.5\ V$; $T_j = 25\ ^\circ C$	-	-	-1	μA
		$V_{GS} = 2.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	100	nA
		$V_{GS} = -2.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = -4.5\ V$; $I_D = -410\ mA$; $T_j = 25\ ^\circ C$	-	1.2	1.4	Ω
		$V_{GS} = -4.5\ V$; $I_D = -410\ mA$; $T_j = 150\ ^\circ C$	-	2	2.4	Ω
		$V_{GS} = -2.5\ V$; $I_D = -320\ mA$; $T_j = 25\ ^\circ C$	-	1.7	2.3	Ω
		$V_{GS} = -1.8\ V$; $I_D = -80\ mA$; $T_j = 25\ ^\circ C$	-	2.1	3.1	Ω
		$V_{GS} = -1.5\ V$; $I_D = -10\ mA$; $T_j = 25\ ^\circ C$	-	3	5.1	Ω

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
g_{fs}	forward transconductance	$V_{DS} = -10\text{ V}$; $I_D = -410\text{ mA}$; $T_j = 25\text{ }^{\circ}\text{C}$		-	820	-	mS
TR1 (N-channel), Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$V_{DS} = 15\text{ V}$; $I_D = 590\text{ mA}$; $V_{GS} = 4.5\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$		-	0.6	1.05	nC
Q_{GS}	gate-source charge			-	0.1	-	nC
Q_{GD}	gate-drain charge			-	0.1	-	nC
C_{iss}	input capacitance	$V_{DS} = 15\text{ V}$; $f = 1\text{ MHz}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$		-	30.3	-	pF
C_{oss}	output capacitance			-	5.8	-	pF
C_{rss}	reverse transfer capacitance			-	4.2	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}$; $I_D = 590\text{ mA}$; $V_{GS} = 4.5\text{ V}$; $R_{G(ext)} = 6\text{ }\Omega$; $T_j = 25\text{ }^{\circ}\text{C}$		-	4	-	ns
t_r	rise time			-	7	-	ns
$t_{d(off)}$	turn-off delay time			-	12	-	ns
t_f	fall time			-	3	-	ns
TR2 (P-channel), Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$V_{DS} = -15\text{ V}$; $I_D = -410\text{ mA}$; $V_{GS} = -4.5\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$		-	0.7	1.2	nC
Q_{GS}	gate-source charge			-	0.17	-	nC
Q_{GD}	gate-drain charge			-	0.16	-	nC
C_{iss}	input capacitance	$V_{DS} = -15\text{ V}$; $f = 1\text{ MHz}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$		-	43.2	-	pF
C_{oss}	output capacitance			-	5.9	-	pF
C_{rss}	reverse transfer capacitance			-	4.2	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -15\text{ V}$; $I_D = -410\text{ mA}$; $V_{GS} = -4.5\text{ V}$; $R_{G(ext)} = 6\text{ }\Omega$; $T_j = 25\text{ }^{\circ}\text{C}$		-	3	-	ns
t_r	rise time			-	4	-	ns
$t_{d(off)}$	turn-off delay time			-	14	-	ns
t_f	fall time			-	5	-	ns
TR1 (N-channel), Source-drain diode characteristics							
V_{SD}	source-drain voltage	$I_S = 380\text{ mA}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$		-	0.86	1.2	V
TR2 (P-channel), Source-drain diode characteristics							
V_{SD}	source-drain voltage	$I_S = -410\text{ mA}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$		-	-0.95	-1.2	V

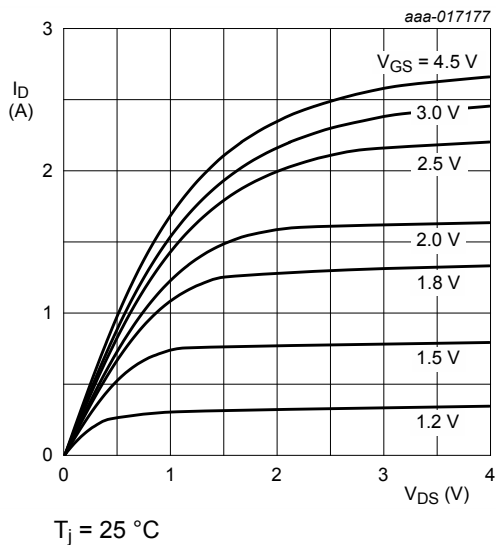


Fig. 8. TR1: Output characteristics: drain current as a function of drain-source voltage; typical values

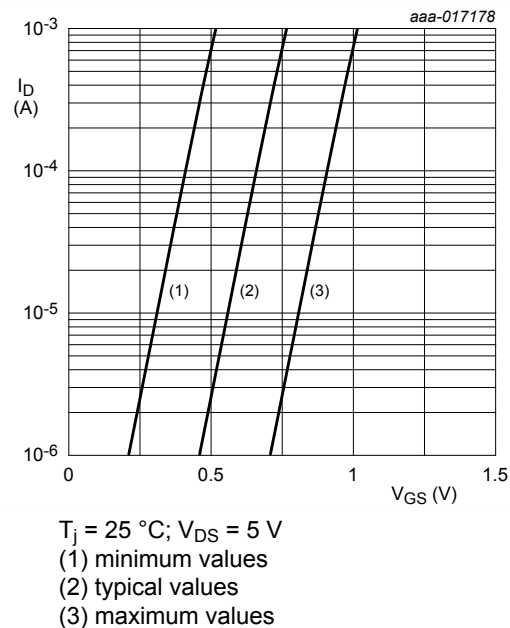


Fig. 9. TR1: Sub-threshold drain current as a function of gate-source voltage

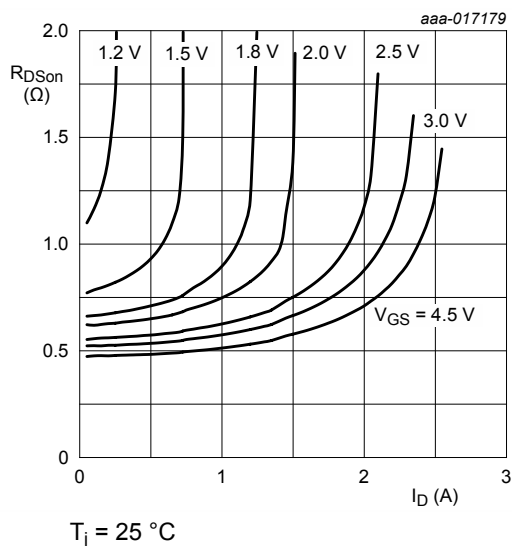


Fig. 10. TR1: Drain-source on-state resistance as a function of drain current; typical values

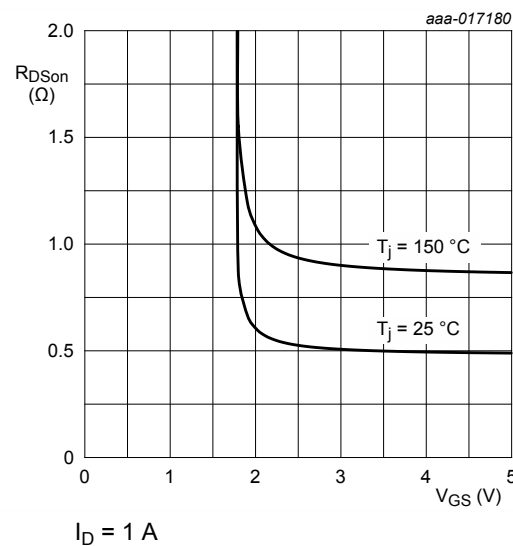


Fig. 11. TR1: Drain-source on-state resistance as a function of gate-source voltage; typical values

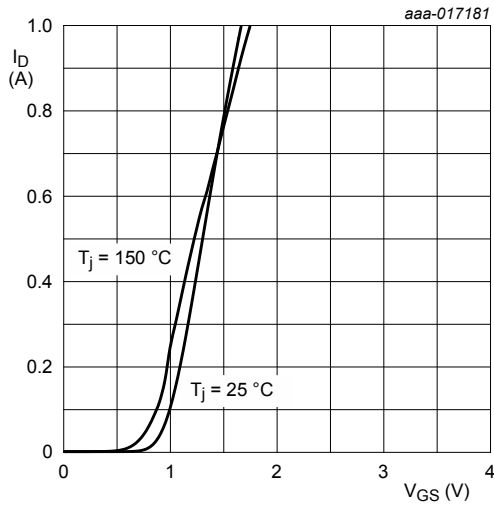


Fig. 12. TR1: Transfer characteristics: drain current as a function of gate-source voltage; typical values

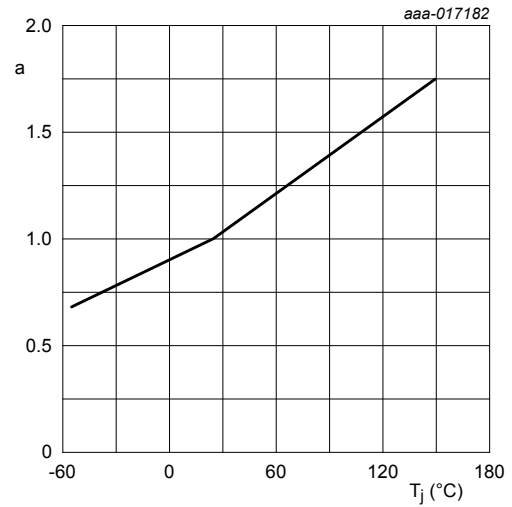


Fig. 13. TR1: Normalized drain-source on-state resistance as a function of junction temperature; typical values

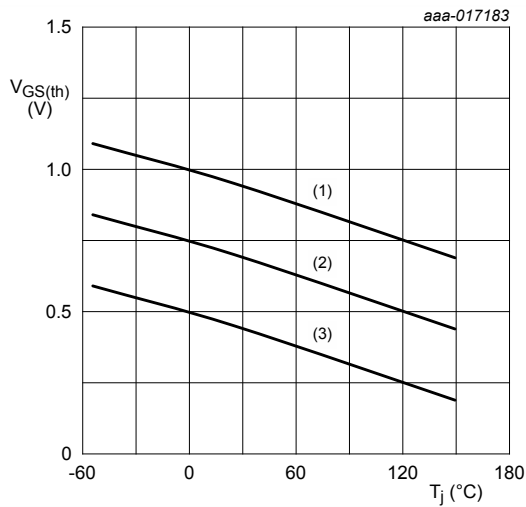


Fig. 14. TR1: Gate-source threshold voltage as a function of junction temperature

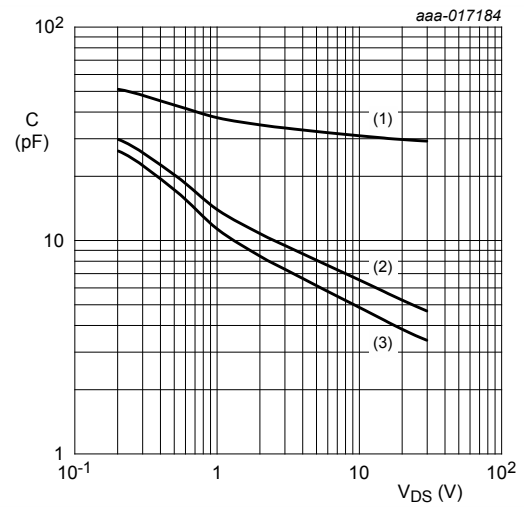


Fig. 15. TR1: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

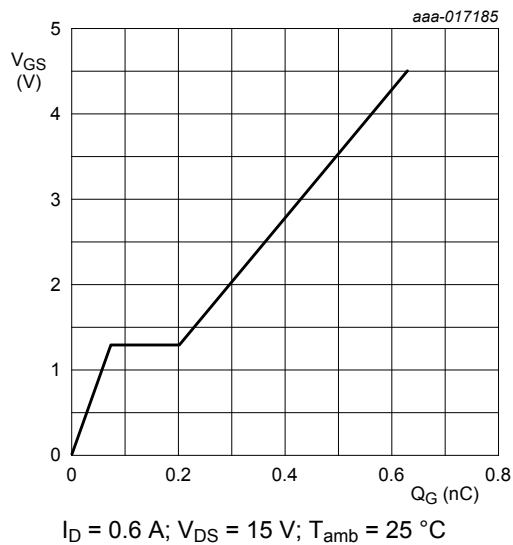


Fig. 16. TR1: Gate-source voltage as a function of gate charge; typical values

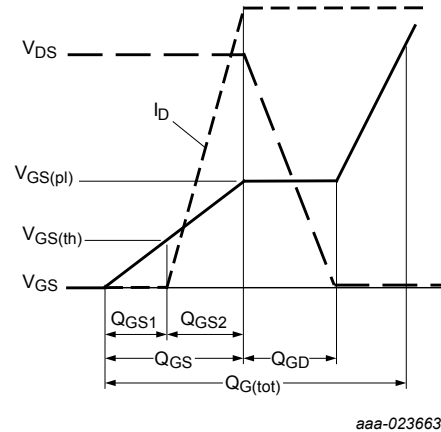


Fig. 17. TR1: Gate charge waveform definitions

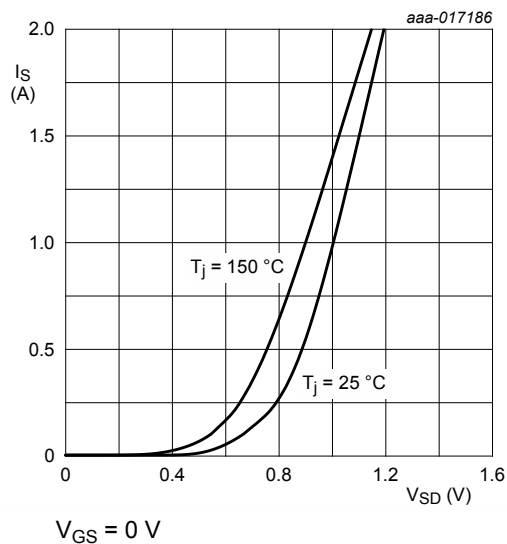


Fig. 18. TR1: Source current as a function of source-drain voltage; typical values

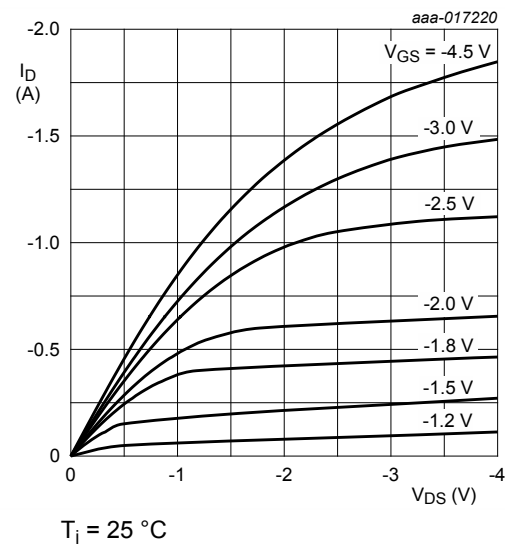


Fig. 19. TR2: Output characteristics: drain current as a function of drain-source voltage; typical values

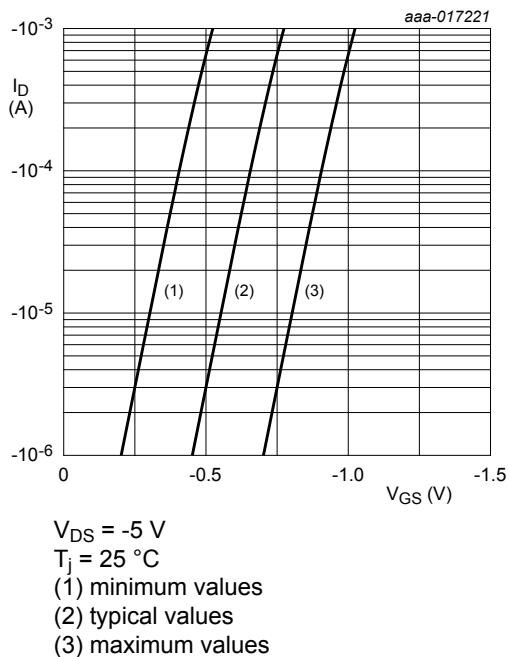


Fig. 20. TR2: Sub-threshold drain current as a function of gate-source voltage

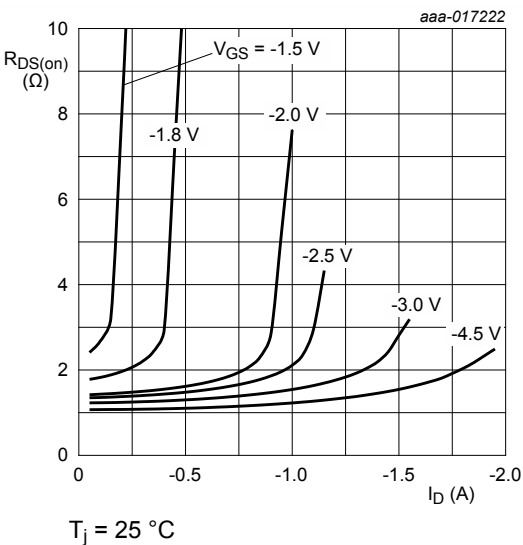


Fig. 21. TR2: Drain-source on-state resistance as a function of drain current; typical values

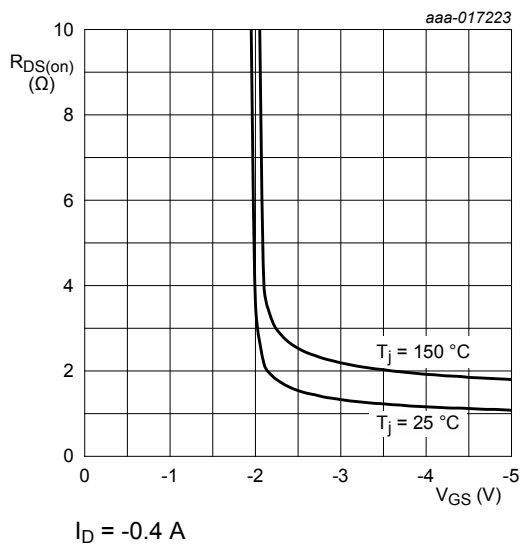


Fig. 22. TR2: Drain-source on-state resistance as a function of gate-source voltage; typical values

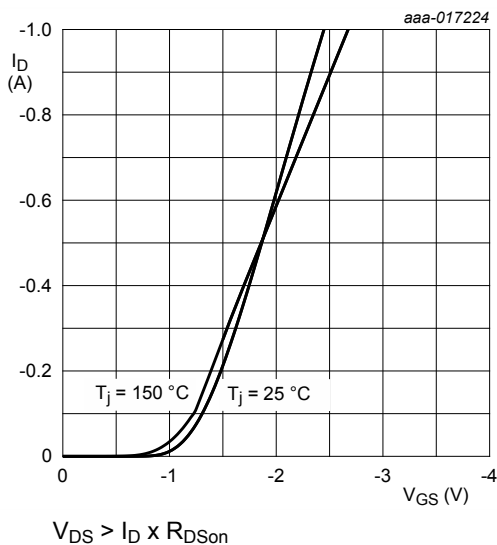
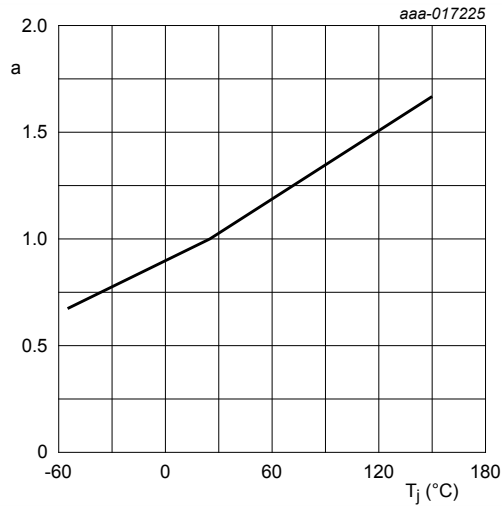
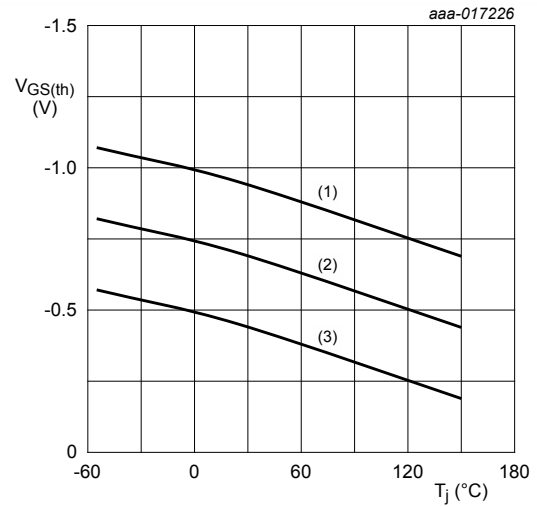


Fig. 23. TR2: Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

Fig. 24. TR2: Normalized drain-source on-state resistance as a function of ambient temperature; typical values



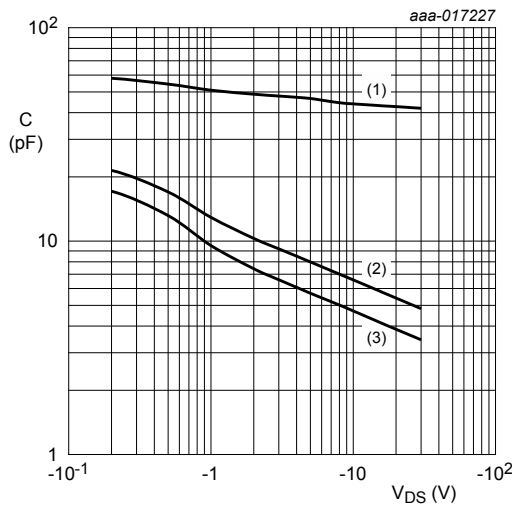
$I_D = -250 \mu\text{A}$; $V_{DS} = V_{GS}$

(1) maximum values

(2) typical values

(3) minimum values

Fig. 25. TR2: Gate-source threshold voltage as a function of junction temperature



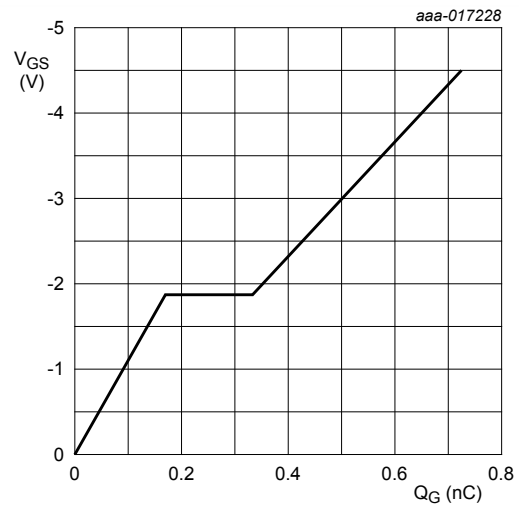
$f = 1 \text{ MHz}$; $V_{GS} = 0 \text{ V}$

(1) C_{iss}

(2) C_{oss}

(3) C_{rss}

Fig. 26. TR2: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{DS} = -15 \text{ V}$; $I_D = -410 \text{ mA}$ $T_{amb} = 25^{\circ}\text{C}$

Fig. 27. TR2: Gate-source voltage as a function of gate charge; typical values

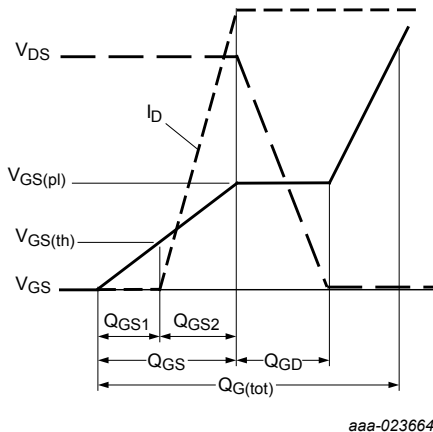


Fig. 28. TR2: Gate charge waveform definitions

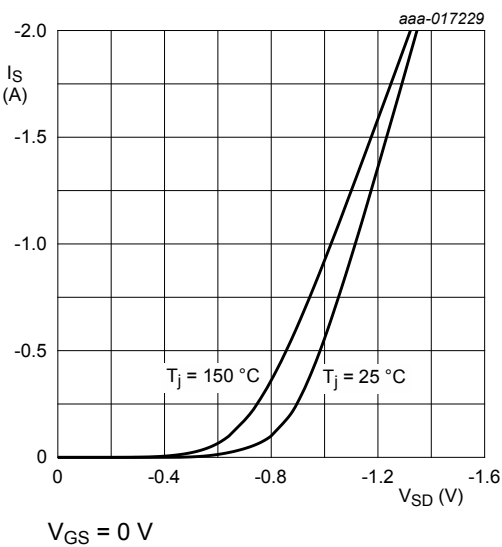


Fig. 29. TR2: Source current as a function of source-drain voltage; typical values

11. Test information

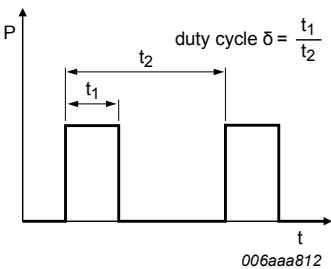
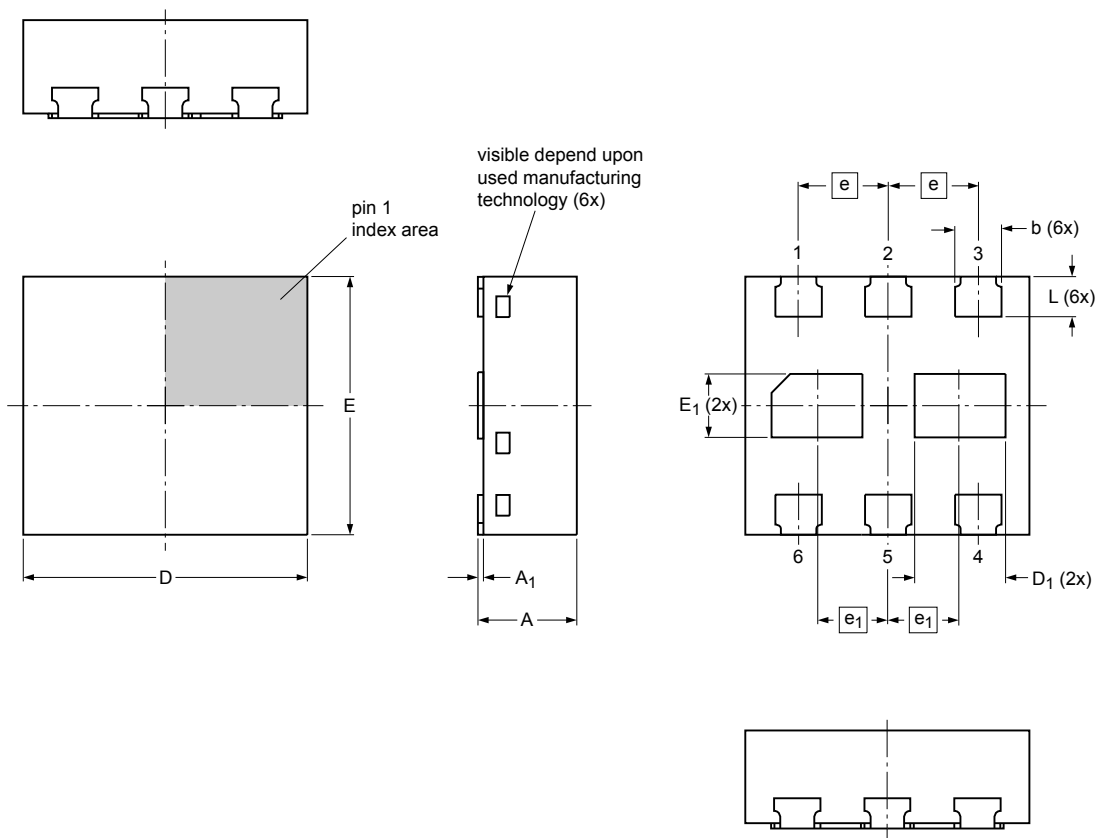


Fig. 30. Duty cycle definition

12. Package outline

DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads;
6 terminals; body: 1.1 x 1.0 x 0.37 mm

SOT1216



0 1 mm
scale

Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	D	D ₁	E	E ₁	e	e ₁	L
min	0.34		0.15	1.05	0.32	0.95	0.22			0.125
mm	nom		0.18	1.10	0.35	1.00	0.25	0.35	0.275	0.155
	max	0.40	0.23	1.15	0.40	1.05	0.30			0.205

Note
1. Dimension A is including plating thickness.

sot1216_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1216						-13-03-05- 13-03-06

Fig. 31. Package outline DFN1010B-6 (SOT1216)

13. Soldering

Footprint information for reflow soldering of DFN1010B-6 package

SOT1216

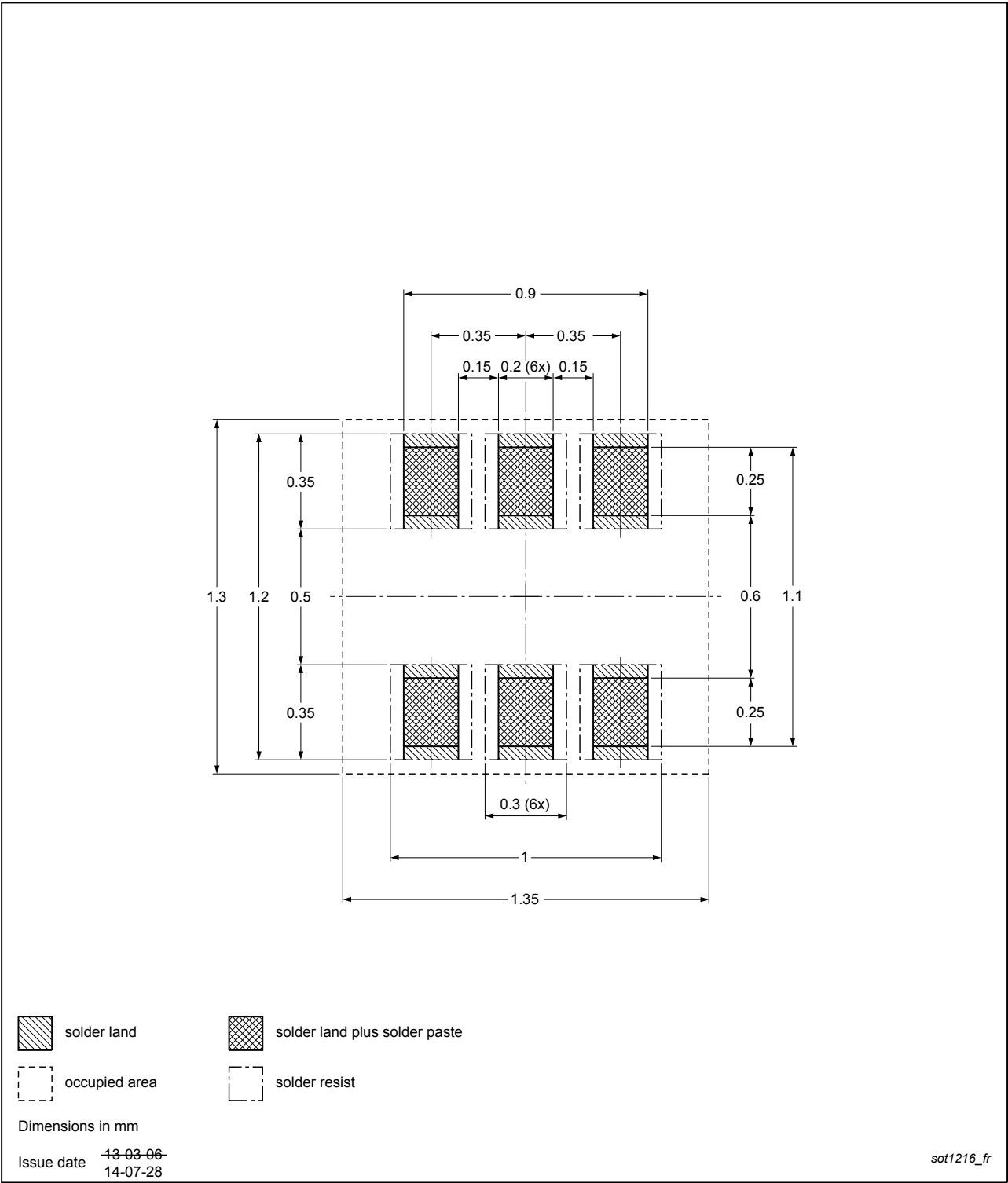


Fig. 32. Reflow soldering footprint for DFN1010B-6 (SOT1216)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMCXB1000UE v.1	20160627	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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16. Contents

1. General description..... 1

2. Features and benefits..... 1

3. Applications..... 1

4. Quick reference data..... 1

5. Pinning information.....2

6. Ordering information.....2

7. Marking.....2

8. Limiting values..... 3

9. Thermal characteristics..... 5

10. Characteristics.....7

11. Test information..... 14

12. Package outline..... 15

13. Soldering..... 16

14. Revision history.....17

15. Legal information..... 18

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